

Form PTO 1449 U.S. Department of commerce Patent and Trademark Office Information Disclosure Statement by Applicant	ATTY. DOCKET NUMBER	SERIAL NUMBER
	NITT.0154	To be assigned 10/64961 3
	APPLICANT	
	FUJISAKI et al.	
	FILING DATE	GROUP
Concurrently herewith		

U.S. Patent Documents

Examiner Initial	Cited by Examiner in parent	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB-CLASS	FILING DATE
W	X	2002-0111000	08/15/02	Kawakami et al.			04/17/02
W	X	6,368,923	04/09/02	Huang, Kuo-Tai			04/28/00
W	X	6,348,420	02/19/02	Raajimakers et al			12/23/99
W	X	6,309,932	10/30/01	Ma et al.			06/16/99
W	X	5,043,224	08/27/91	Jaccodine et al			04/05/90

Foreign Patent Documents

Examiner Initial	DOCUMENT NUMBER	FILING DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION	
						YES	No
W	2000-269483	3/19/1999	Japan			Abstract	X
W	55-145373	4/28/1979	Japan			Abstract	X
W	10-135207	10/8/1997	Japan			Abstract	X
W	11-126902	8/3/1998	Japan			Abstract	X
W	58-040833	9/4/1981	Japan			Abstract	X

Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

W	Phillip J. Caplan, Edward H. Poindexter, Bruce E. Deal and Reda R. Razouk, "ESR Centers, Interface States, and Oxide Fixed Charge in Thermally Oxidized Silicon Wafers", J. Appl. Phys. 50(9), September 1979, pp. 5847-5854
W	F. B. McLean, "A Framework for Understanding Radiation-Induced Interface States in SiO ₂ MOS Structures", IEEE Transactions on Nuclear Science, Vol. NS-27, No. 6, December 1980, pp. 1651-1657

EXAMINER <i>W J QRC</i>	DATE CONSIDERED 2/20/05
Examiner: Initial if citation is considered, whether or not citation is in conformance with MPEP 609; draw a line through citation if not in conformance and not considered. Include a copy of this form with next communication to applicant	